






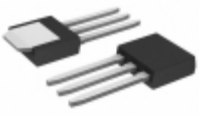
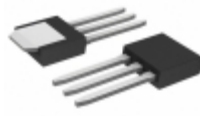




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|  | <h2 style="color: #E67E22;">GP1M003A080CH</h2> | |
| | Hersteller-Teilenummer: | GP1M003A080CH |
|  | Hersteller / Marke: | Global Power Technologies Group |
| | Teil der Beschreibung: | MOSFET N-CH 800V 3A DPAK |
| Datenblätter: |  GP1M003A080CH.pdf | |
| RoHs Status: | Bleifrei / RoHS-konform | |
| Lagerzustand: | New original, 5000 pcs Stock Available. | |
| Liefern von: | Hong Kong | |
| Versandweg: | DHL/Fedex/TNT/UPS/EMS | |
| <p>Image may be representation. See specs for product details.</p> | | |

Spezifikationen

| | |
|--|---|
| Teilenummer | GP1M003A080CH |
| Hersteller | Global Power Technologies Group |
| Beschreibung | MOSFET N-CH 800V 3A DPAK |
| Kategorie | Diskrete Halbleiterprodukte > Transistoren-FETs, |
| Teilstatus | 5000 pcs Stock |
| Serie | - |
| Technologie | MOSFET (Metal Oxide) |
| Betriebstemperatur | -55°C ~ 150°C (TJ) |
| Befestigungsart | Surface Mount |
| Verpackung / Gehäuse | TO-252-3, DPak (2 Leads + Tab), SC-63 |
| Supplier Device-Gehäuse | TO-252, (D-Pak) |
| Verlustleistung (max) | 94W (Tc) |
| Typ FET | N-Channel |
| FET-Merkmal | - |
| Drain-Source-Spannung (Vdss) | 800V |
| Strom - Ununterbrochener Abfluss (Id) bei 25 ° C | 3A (Tc) |
| Rds On (Max) @ Id, Vgs | 4.2 Ohm @ 1.5A, 10V |
| VGS (th) (Max) @ Id | 4V @ 250µA |
| Gate Charge (Qg) (Max) @ Vgs | 19nC @ 10V |
| Eingabekapazität (Ciss) (Max) @ Vds | 696pF @ 25V |
| Verpackung | Tape & Reel (TR) |

GP1M003A080CH ist neu im Original, Suche GP1M003A080CH Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie GP1M003A080CH Global Power Technologies Group mit Garantie und Vertrauen. Anfrage GP1M003A080CH: Info@Y-IC.com

Sie können auch interessiert sein:

| | | | |
|--|--|---|--|
|  <p>GP1M003A050PG Global Power Technologies Group MOSFET N-CH 500V 2.5A IPAK</p> |  <p>GP1M003A050CG Global Power Technologies Group MOSFET N-CH 500V 2.5A DPAK</p> |  <p>GP1M003A090PH Global Power Technologies Group MOSFET N-CH 900V 2.5A IPAK</p> |  <p>GP1M003A080PH Global Power Technologies Group MOSFET N-CH 800V 3A IPAK</p> |
|  <p>GP1M003A040PG Global Power Technologies Group MOSFET N-CH 400V 2A IPAK</p> |  <p>GP1M003A080H Global Power Technologies Group MOSFET N-CH 800V 3A TO220</p> |  <p>GP1M003A090C Global Power Technologies Group MOSFET N-CH 900V 2.5A DPAK</p> |  <p>GP1M003A080FH Global Power Technologies Group MOSFET N-CH 800V 3A TO220F</p> |

heiße Teile

Mehr

| | | | | |
|-----------------|-----------------|-----------------|-----------------|-----------------|
| ⚙ GP1A75EJ000F | ↔ GP1A75LBJ00F | ⇒ GP1FA501RZ | D GP1FA501TZ | ↔ GP1FA502RZ |
| ⊣ GP1FA513TZ | ⚙ GP1FA51TKOF | D GP1FA550RZ | ⇒ GP1FA550TZ | ↔ GP1FA551 |
| ⚙ GP1FA551TZ | ⊣ GP1FA553RZ0F | ⚙ GP1FA553RZ0F | ↔ GP1FA553TZ0F | ↔ GP1FAV31TK0F |
| D GP1FAV50RK0F | ⚙ GP1FAV50TK0F | ⊣ GP1FAV51TK0F | ⚙ GP1FD320TP0F | ↔ GP1FM313TMF5 |
| ⇒ GP1FM313TZMF | ↔ GP1FSV51TK0F | ⚙ GP1L53VJ000F | ⊣ GP1L57J0000F | ↔ GP1M003A050FG |
| ↔ GP1M003A090C | ⇒ GP1M006A070FH | D GP1M007A090H | ⚙ GP1M008A025PG | ⊣ GP1M009A020FG |
| ⚙ GP1M009A090N | D GP1M010A060H | ⇒ GP1M010A080FH | ↔ GP1M011A050FH | ↔ GP1M013A050H |
| ⊣ GP1M016A025CG | ⚙ GP1M016A060F | ↔ GP1M016A060H | ⇒ GP1S092HCPI | ↔ GP1S092HCPIF |
| ⚙ GP1S092HCPIF | ⊣ GP1S092HCPKF | ⚙ GP1S093HCZ | D GP1S093HCZ0F | ↔ GP1S093HCZ0F |
| ↔ GP1S093HCZ0F | ⚙ GP1S094HCZ0F | ⊣ GP1S094HCZ0F | ⚙ GP1S094HCZ0F | ↔ GP1S096HCZ |

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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